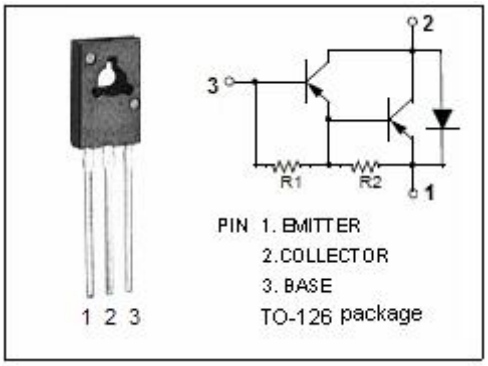
isc Silicon PNP Darlington Power Transistor 2SB1272

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -100V(Min)
- High DC Current Gain-
  : h_{FE}=1000(Min)@ (V_{CE}= -2V, I_C= -1A)
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

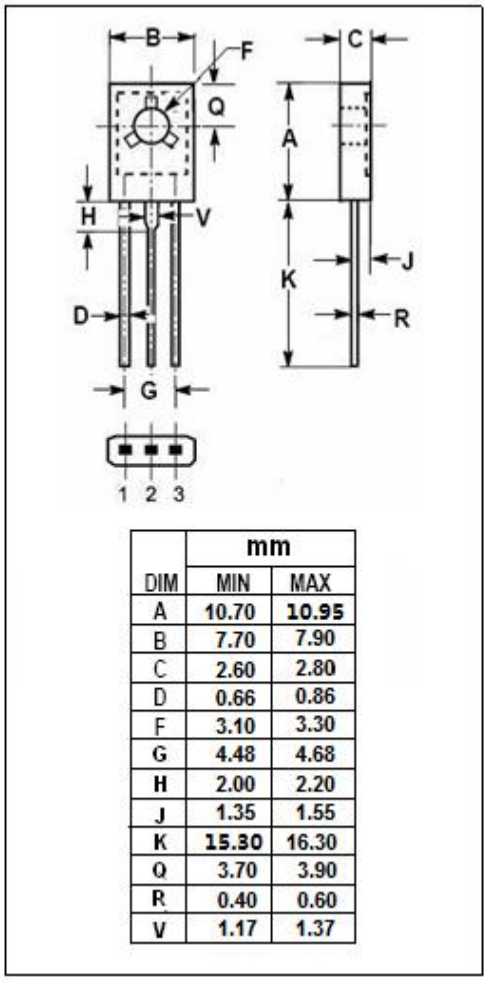


APPLICATIONS

- Designed for low frequency power amplifiers applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-2	A
I_{CM}	Collector Current-Peak	-5	A
P_C	Collector Power Dissipation @T_C=25℃	40	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃



DIM	mm MIN	MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA; R_{BE}= ∞	-100			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -5mA; I_C= 0	-7			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -2A; I_B= -2mA			-2.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -2A; I_B= -2mA			-2.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -100V; I_E= 0			-100	μA
I_{CEO}	Collector Cutoff Current	V_{CE}= -100V; R_{BE}= ∞			-500	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -7V; I_C= 0			-5.0	mA
h_{FE}	DC Current Gain	I_C= -1A; V_{CE}= -2V	1000		10000	
C_{OB}	Output Capacitance	I_E=0; V_{CB}= -10V; f= 0.1MHz	35			pF
Switching Times						
t_{on}	Turn-on Time	I_C= -2A, I_{B1}= -I_{B2}= -2mA		0.5		μs
t_{stg}	Storage Time			3.0		μs
t_f	Fall Time			1.0		μs